What is claimed is:

1. A method for forming a double density wordline, comprising:

providing a semiconductor substrate;

sequentially forming a poly layer, a first insulating layer, a first sacrificial layer, a second insulating layer, and a photoresist layer with a wordline pattern on the semiconductor substrate;

sequentially etching the second insulating layer and the first sacrificial layer using the photoresist layer as an etching mask until the first insulating layer is exposed to form a first wordline mask, a second wordline mask, and an opening therebetween;

removing the photoresist layer;

forming a spacer on a sidewall of the opening;

forming a second sacrificial layer in the opening;

removing the spacer, the second insulating layer, and the first insulating layer under the spacer to form a third wordline mask composed of the second sacrificial layer and the first insulating layer thereunder; and

etching the poly layer to form a first wordline, a second wordline, and a third wordline using the first wordline mask, the second wordline mask, and the third wordline mask as etching masks.

2. The method for forming a double density wordline of claim 1, further comprising a silicide layer over the surface of the poly layer.

3. The method for forming a double density wordline of claim 2, wherein the silicide layer is a tungsten silicide layer.

4. The method for forming a double density wordline of claim 3, wherein a thickness of the tungsten silicide layer is 1550 to 1650Å.

5. The method for forming a double density wordline of claim 1, wherein a thickness of the poly layer is 1150 to 1250Å.

6. The method for forming a double density wordline of claim 1, wherein the first insulating layer is a silicon oxide layer.

7. The method for forming a double density wordline of claim 6, wherein a thickness of the silicon oxide layer is 750 to 850Å.

8. The method for forming a double density wordline of claim 1, wherein the first sacrificial layer is a poly layer.

9. The method for forming a double density wordline of claim 8, wherein a thickness of the poly layer is 950 to 1050Å.

10. The method for forming a double density wordline of claim 1, wherein the second insulating layer is a nitride layer.

11. The method for forming a double density wordline of claim 10, wherein a thickness of the nitride layer is 250 to 350Å.

12. The method for forming a double density wordline of claim 1, wherein the spacer is a nitride layer.

13. The method for forming a double density wordline of claim 1, wherein the second sacrificial layer is a poly layer.

14. A method for forming a double density wordline, comprising:

providing a semiconductor substrate with a poly layer, a silicide layer, a oxide layer, a first dummy poly layer, and a first nitride layer;

forming a photoresist layer with a first opening on the nitride layer, wherein a portion of the first nitride layer is exposed by the first opening;

sequentially etching the fist nitride layer and the first dummy poly layer until the oxide layer is exposed to form a first wordline mask, a second wordline mask, and a second opening therebetween;

removing the photoresist layer;

conformably forming a second nitride layer cover the first wordline mask, the second wordline mask, and the second opening;

anisotropically etching the second nitride layer to form a spacer on a sidewall of the second opening;

forming a second dummy poly layer cover the first wordline mask, the second wordline mask, and the second

opening, wherein the second opening is filled with the second dummy poly layer;

etching the second dummy poly layer to a level below the spacer;

removing the spacer, the first nitride layer, and the exposing oxide layer to form a third wordline mask composes of the second dummy poly layer and the oxide thereunder; and

sequentially etching the silicide layer and the poly layer to form a first wordline, a second wordline, a third wordline using the first wordline mask, the second wordline mask, and the third wordline mask as etching masks.

15. The method for forming a double density wordline of claim 14, further comprising a step to remove the first wordline mask, the second wordline mask, and the third wordline mask.

16. The method for forming a double density wordline of claim 14, wherein a thickness of the poly layer is 1150 to 1250Å.

17. The method for forming a double density wordline of claim 14, wherein the silicide layer is a tungsten silicide layer.

18. The method for forming a double density wordline of claim 17, wherein a thickness of the tungsten silicide layer is 1550 to 1650Å.

19. The method for forming a double density wordline of claim 14, wherein a thickness of the oxide layer is 750 to 850Å.

20. The method for forming a double density wordline of claim 14, wherein a thickness of the first dummy poly layer is 950 to 1050Å.

21. The method for forming a double density wordline of claim 14, wherein a thickness of the first nitride layer is 250 to 350Å.

22. The method for forming a double density wordline of claim 14, wherein a thickness of the second nitride layer is 400Å.

23. The method for forming a double density wordline of claim 14, wherein the anisotropic etching is reactive ion etching or plasma etching.

24. The method for forming a double density wordline of claim 14, wherein a thickness of the second dummy poly layer is 2000Å.